

# ME2139



# ULTRA-SMALL PACKAGE PWM/PFM SWITCHING CONTROL

#### STEP-UP SWITCHING REGULATOR

### **General Description**

The ME2139 series is a CMOS step-up switching regulator which mainly consists of a reference voltage source, an oscillation circuit, an error amplifier, a phase compensation circuit, a PWM/PFM switching control circuit. With an external low-ON-resistance Nch Power MOS, this product is applicable to applications requiring high efficiency and high output current. The ME2139 series switches its operation to the PFM control circuit whose duty ratio is 15 % with to the PWM/PFM switching control circuit under a light load and to prevent decline in the efficiency by IC operation current.

#### **Features**

- Low voltage operation: Start-up is guaranteed from 0.9 V(IOUT =1 mA)
- Duty ratio: Built-in PWM/PFM switching control circuit 15 to 78 %.
- oscillator frequency: 1.0MHz
- External parts: coil, diode, capacitor, and transistor
- Output voltage range: 1.5V-20V
- Output voltage accuracy: ±2%
- Soft start function: 2 ms

### **Applications**

- MP3 players, digital audio players
- Digital cameras, GPS, wireless transceiver
- Portable devices

### **Package**

• 5-pin SOT23-5



# **Typical Application Circuit**

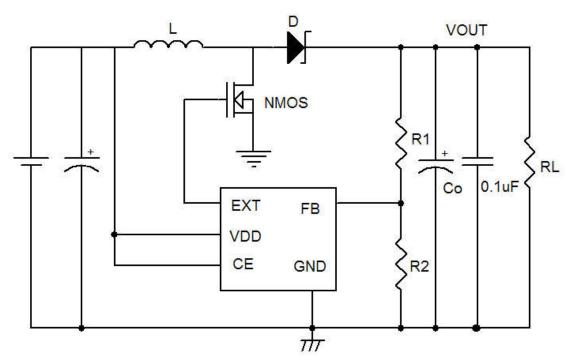
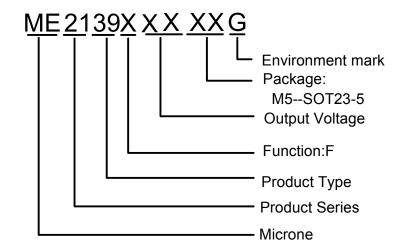


Fig.1 For Feedback and external

V03 <u>www.microne.com.cn</u> Page 2 of 12

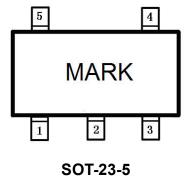


### **Selection Guide**



product series	switching transistor	CE function	VDD function	FB function	features
ME2139FM5G	External Transistor	Yes	Yes	Yes	Ext +Feedback

## **Pin Configuration**



## **Pin Assignment**

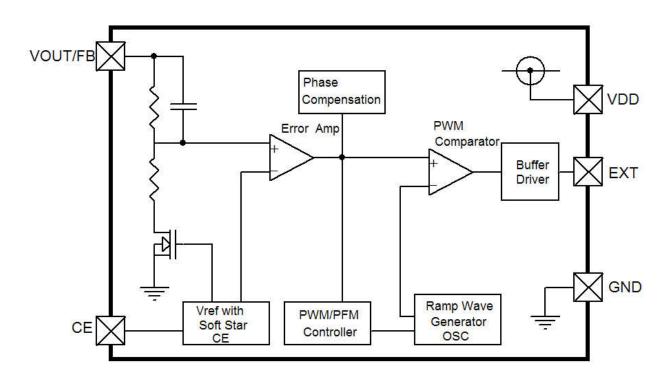
#### **ME2139FM5G**

Pin Number	Pin Name	Function		
SOT-23-5	1 III I I I III			
1	FB	Feed Back voltage pin		
2	VDD	IC power supply pin		
3	CE	Shutdown pin		
4	GND	GND pin		
5	EXT	External transistor connection pin		

V03 <u>www.microne.com.cn</u> Page 3 of 12



## **Block Diagram**



# **Absolute Maximum Rangs**

PARAMETER	SYMBOL	RATINGS	UNITS
VDD Pin Voltage	VDD	-0.3~6.5	V
EXT Pin Voltage	EXT	-0.3∼VDD+0.3	V
VOUT Pin Voltage	VOUT	-0.3∼6.5	V
CE Pin Voltage	VCE	-0.3∼Vin+0.3	V
EXT Pin Voltage	IEXT	±1000	mA
Power Dissipation (SOT23-5)	Pd	300	mW
Operating Temperature Range	$T_{Opr}$	-25~+85	$^{\circ}\mathbb{C}$
Storage Temperature Range	T <sub>stg</sub>	-40~+125	$^{\circ}\mathbb{C}$

V03 <u>www.microne.com.cn</u> Page 4 of 12



### **Electrical Characteristics**

#### ME2139FxxG

Measuring conditions: VDD=VCE=3.3V, Topt=25 $^{\circ}$ C  $_{\circ}$  Unless otherwise specified  $_{\circ}$ 

Parameter	SYMBOL	CON	DITION	MIN	TYP	MAX	UNIT	Circuit
Feedback voltage	$V_{FB}$	-		1.225	1.25	1.275	V	2
Input voltage	V <sub>IN</sub>	-			-	6	V	2
Operation start voltage	V <sub>ST</sub>	I <sub>OUT</sub> =1mA		-	-	0.9	<b>V</b>	2
Operation holding voltage	$V_{HLD}$	I <sub>оυт</sub> =1mA,Measured b gradually	by decreasing VIN voltage	0.7	-	-	٧	2
Current consumption 1	I <sub>SS1</sub>	V <sub>FB</sub> =V <sub>FB</sub> (S)× 0.95		-	200	ı	μΑ	1
Current consumption 2	I <sub>SS2</sub>	V <sub>FB</sub> =1.5V		-	15	-	μA	1
Current consumption during shutdown	I <sub>SSS</sub>	V <sub>CE</sub> =0V		-	0.02	0.5	μA	1
EXT pin output	I <sub>EXTH</sub>	V <sub>EXT</sub> =V <sub>OUT</sub> -0.4V		-	-25	-	mA	1
current	I <sub>EXTL</sub>	V <sub>EXT</sub> =0.4V			40	-	mA	1
Feed back voltagetemperature coefficient		Ta=-25-85℃		-	±50	-	ppm/°C	2
Oscillation frequency	Fosc	-		8.0	1.0	1.2	MHz	1
Max. duty ratio	MAXDUTY	V <sub>FB</sub> =V <sub>FB</sub> (S)× 0.95		-	78	-	%	1
PWM/PFM switchingduty ratio	PFMDUTY	V <sub>FB</sub> =V <sub>FB</sub> (S)× 1.5, no load		-	15	1	%	1
Shutdown pin input voltage	$V_{SH}$	Measured the oscillation at EXT pin		0.75	-	-	V	1
	V <sub>SL1</sub>	Judged the stop of oscillation at EXT pin	V <sub>OUT</sub> ≥1.5V	-	-	0.3	V	1
	V <sub>SL2</sub>		V <sub>OUT</sub> <1.5V	-	-	0.2	V	1
Shutdown pin input	I <sub>SH</sub>	V <sub>CE</sub> =V <sub>FB</sub> (S)×0.95		-0.1	-	0.1	μA	1
voltage	I <sub>SL</sub>	V <sub>CE</sub> =0V		-0.1	-	0.1	μΑ	1
Soft start time	tss	-		-	2	-	mS	2
Efficiency	EFFI	-		-	90	-	%	2

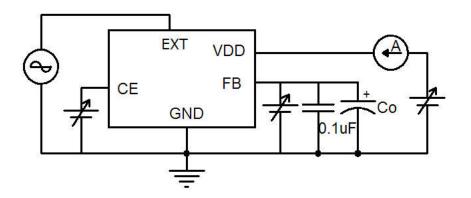
- 1. VOUT(S) is the set output voltage value,and VOUT is the typital value of the output voltage.
- 2. VOUT(S) can be set by using the rate of VFB and output voltage setting resisitors(R1,R2).
- 3. VFB(S) is the set output voltage value.
- 4. This product from the start when the VDD=0.9V booster work , but in order to stabilize the output voltage and oscillation frequency ,to control the VDD, 2.5V ≤ VDD<6V.

V03 <u>www.microne.com.cn</u> Page 5 of 12

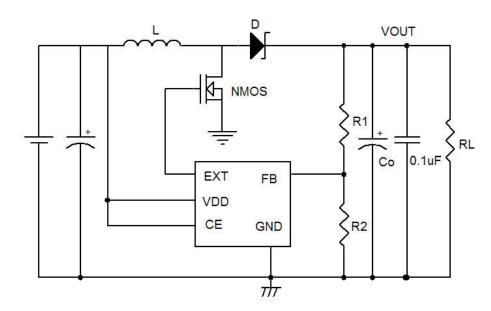


### **Test Circuit:**

1.



2.



## **External parts (suggest)**

- 1. Diode use Schottky diode such as SS14 or SS34 forward voltage drop:0.2V)
- 2、NMOS: MEM8205 or MEM2310
- 3. Inductor:  $3.3\mu H (r<0.5\Omega)$
- 4. Capacitor: Tantalum type 22uF
- 5 Feed back resistors:R1+R2<50K

V03 <u>www.microne.com.cn</u> Page 6 of 12



### External parts selection for DC/DC converter

The relationship between major characteristics of the step-up circuit and characteristics parameters of the external parts are shown in Figure 1.

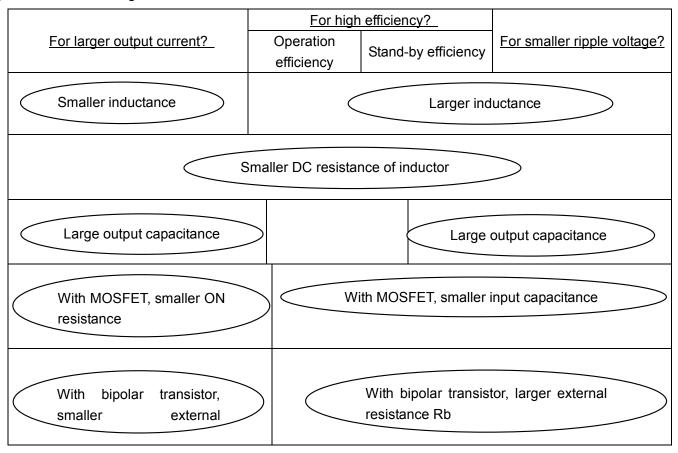


Figure 1 Relationship between major characteristics of the step-up circuit and external parts

#### 1. Inductor

An inductance has strong influence on maximum output current  $I_{OUT}$  and efficiency  $\eta.1$ .

Figure 2 shows the relation between  $I_{OUT}$ , and  $\eta$  characteristics to L of ME2139F.

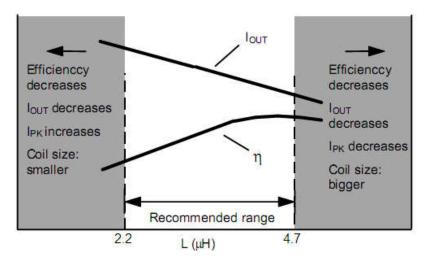


Figure 2 L—louτ and η characteristics

The peak current (I<sub>PK</sub>) increases by decreasing L and the stability of a circuit improves and I<sub>OUT</sub> increases. If L is

V03 www.microne.com.cn Page 7 of 12



furthermore made small, efficiency falls and in running short,  $l_{OUT}$  decreases. (Based on the current drive capability of external switching transistor.)

The loss of  $I_{PK}$  by the switching transistor decreases by increasing L and the efficiency becomes maximum at a certain L value. Further increasing L decreases efficiency due to the loss of DC resistance of the coil. Also,  $b_{UT}$  decreases, too.

Oscillation frequency is higher, smaller one can be chose and also makes coil smaller. The recommended inductances are 2.2 to 4.7 µH inductor for ME2139F.

Choose a value for L by referring to the reference data because the maximum output current is due to the input voltage in an actual case. Choose an inductor so that  $I_{PK}$  does not exceed the allowable current. Exceeding the allowable current of the inductor causes magnetic saturation, remarkable low efficiency and destruction of the IC chip due to a large current.

IPK in uncontinuous mode is calculated from the following equation:

$$I_{PK} = \sqrt{\frac{2I_{OUT}(V_{OUT} + V_D - V_{IN})}{f_{OSC}.L}} (A)$$

Fosc = oscillation frequency, VDD =0.4 V.

#### 2. Diode

Use an external diode that meets the following requirements:

Low forward voltage: (VF<0.3 V)</li>

• High switching speed: (50 ns max.)

• Reverse voltage: Vout + VF or more

Rated current: IPK or more

#### 3. Capacitor (CIN, Co)

To improve efficiency, an input capacitor ( $C_{IN}$ ) lowers the power supply impedance and averages the input current. Select  $C_{IN}$  according to the impedance of the power supply used. The recommended capacitance is 10 $\mu$ F for the ME2139F.

An output capacitor ( $C_{OUT}$ ), which is used to smooth the output voltage, requires a capacitance larger than that of the step-down type because the current is intermittently supplied from the input to the output side in the step-up type. A  $22\mu F$  ceramic capacitor is recommended for the ME2139F. However, a higher capacitance is recommended if the output voltage is high or the load current is large. If the output voltage or load current is low, about  $10\mu F$  can be used without problems.

Select C<sub>OUT</sub> after sufficient evaluation with actual application.

A ceramic capacitor can be used for both the input and output.

V03 www.microne.com.cn Page 8 of 12



#### 4. Enhancement MOS FET type

Depending on the MOS FET you use in your device, there is a chance of a current overrun at power ON.

Thoroughly test all settings with your device before deciding on which one to use. Also, try to use a MOS FET with the input capacitance of 700 pF or less.

Since the ON resistor of the MOS FET might depend on the difference between the output voltage VouT and the threshold voltage of MOS FET, and affect the output current as well as the efficiency, the threshold voltage should be low. When the output voltage is low, the circuit operates only when the MOS FET has the threshold voltage lower than the output voltage.

#### 5. Precautions

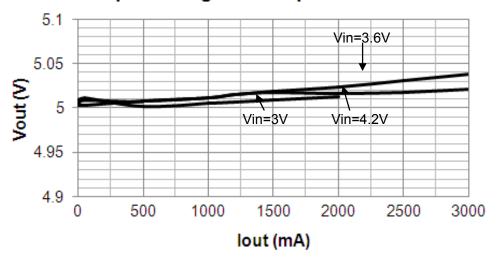
- Mount external capacitors, a diode, and a coil as close as possible to the IC.
- Unique ripple voltage and spike noise occur in switching regulators. Because they largely depend on the coil and the capacitor used, check them using an actually mounted model.
- •Make sure dissipation of the switching transistor (especially at a high temperature) does not exceed the allowable power dissipation of the package.
- •The performance of this IC varies depending on the design of the PCB patterns, peripheral circuits and external parts. Thoroughly test all settings with your device. Also, try to use recommended external parts.

V03 www.microne.com.cn Page 9 of 12

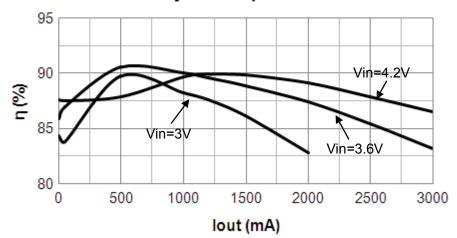


### **Typical Performance Characteristics**

# Output Voltage vs. Output Current



## Efficiency vs. Output Current

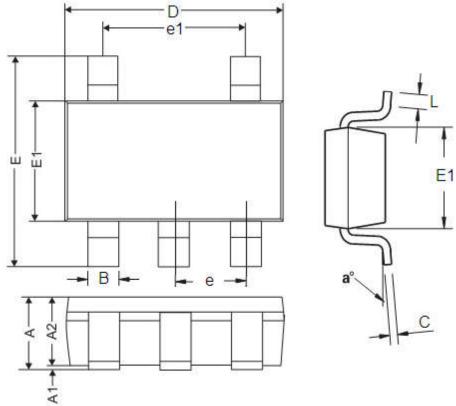


V03 <u>www.microne.com.cn</u> Page 10 of 12



# **Packaging Information**

# • SOT23-5



DIM	Millin	neters	Inches		
DIM	Min	Max	Min	Max	
Α	0.9	1.45	0.0354	0.0570	
A1	0	0.15	0	0.0059	
A2	0.9	1.3	0.0354	0.0511	
В	0.2	0.5	0.0078	0.0196	
С	0.09	0.26	0.0035	0.0102	
D	2.7	3.10	0.1062	0.1220	
E	2.2	3.2	0.0866	0.1181	
E1	1.30	1.80	0.0511	0.0708	
е	0.95REF		0.0374REF		
e1	1.90REF		0.0748REF		
L	0.10	0.60	0.0039	0.0236	
a <sup>0</sup>	00	30°	00	30°	



- The information described herein is subject to change without notice.
- Nanjing Micro One Electronics Inc is not responsible for any problems caused by circuits or diagrams
  described herein whose related industrial properties, patents, or other rights belong to third parties.
  The application circuit examples explain typical applications of the products, and do not guarantee the
  success of any specific mass-production design.
- Use of the information described herein for other purposes and/or reproduction or copying without the express permission of Nanjing Micro One Electronics Inc is strictly prohibited.
- The products described herein cannot be used as part of any device or equipment affecting the human body, such as exercise equipment, medical equipment, security systems, gas equipment, or any apparatus installed in airplanes and other vehicles, without prior written permission of Nanjing Micro One Electronics Inc.
- Although Nanjing Micro One Electronics Inc exerts the greatest possible effort to ensure high quality
  and reliability, the failure or malfunction of semiconductor products may occur. The user of these
  products should therefore give thorough consideration to safety design, including redundancy,
  fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community
  damage that may ensue.

V03 www.microne.com.cn Page 12 of 12